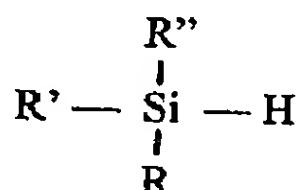


7. (Previously presented) The method of manufacturing a flat panel display where thin film transistor (TFT) and wiring dimensions contained therein are microscopically small and registration of subsequent layers of such display is within microns over many inches, using the method defined in Claim 4.

8) (Previously presented) The method of manufacturing a microelectronic pattern using the method defined in Claim 1.

9) (Currently amended) The method of making a stamp for microcontact printing as defined in Claim 4 wherein said siloxane system contains monomeric monomeric moieties selected from the group consisting of hexamethylcyclotrisiloxane, octamethylcyclotrisiloxane, decamethylcyclotrisiloxane, octaphenylcyclotetrasiloxane, diphenylsilanediol, trimethyltriphenylcyclotrisiloxane, vinylmethylcyclosiloxanes, trifluoropropylmethylcyclosiloxanes, methylhydrocyclosiloxane, hexamethyldisiloxane, divinyltetramethyldisiloxane, tetramethyldisiloxane.

10) (Previously presented) The method of making a stamp for microcontact printing as defined in Claim 4 wherein said siloxane system comprises polydimethyl siloxane oligomers with silyl vinyl groups (-- Si - C = CH₂) and polydimethyl siloxane oligomers with silicon hydride groups having the formula:



wherein R, R', R" are methyl and phenyl, vinyl and hydrogen, which will react with the vinyl groups in the presence of a catalyst to cross-link into a rubber material.